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제21회 한국반도체학술대회
February 24–26, 2014 / Hanyang University, Seoul, Korea

D. Thin Film Process Technology 분과

[WE3-D] Thin-Film Process

Date	Feb. 26, 2014 (Wed.)
Place	Room E / 제1공학관 403호 (# 403, Engineering Building I)

Session Chair: 최창환 교수(한양대학교), 박태주 교수(한양대학교)

- WE3-D-1 15:50-16:05 Electrical Properties of ALD La2O3-Capped High-K/Metal Gate Device**
저자: Donghwan Lim¹, Woosuk Jung¹, Moon-Suk Choi¹, Dohyung Kim¹, Youngil Gil¹, Chulwon Chung², and Changhwan Choi¹
소속: ¹Division of Materials Science and Engineering, Hanyang University, ²Department of Energy Engineering, Hanyang University
- WE3-D-2 16:05-16:20 Oxidizing Agent Effects in Atomic Layer Deposition of HfxZr1-xO2 Thin Films with High Dielectric Constant**
저자: 최민정^{1, 2}, 박형호², 김성근¹
소속: ¹한국과학기술연구원 전자재료연구센터
²연세대학교 신소재공학과
- WE3-D-3 16:20-16:35 Stabilization of Negative Capacitance in Ferroelectric Thin Films**
저자: Yu Jin Kim, Min Hyuk Park, Han Joon Kim, Tae Hwan Moon, and Cheol Seong Hwang
소속: Department of Material Science & Engineering and Inter university Semiconductor Research Center, Seoul National University
- WE3-D-4 16:35-16:50 Effect of NH3 Plasma Treatments on Deposition of Nickel Film by Chemical Vapor Deposition**
저자: Jingyu Park¹, Heeyoung Jeon¹, Hyunjung Kim¹, Jinho Kim², Woochool Jang², and Hyeongtag Jeon^{1, 2}
소속: ¹Department of Nano-scale Semiconductor Engineering, Hanyang University, ²Department of Materials Science and Engineering, Hanyang University,
- WE3-D-5 16:50-17:05 Analysis of a Reaction Mechanism of Oxide Layer Removal using Reactive Gas**
저자: Hyuntae Kim¹, Jungsoo Lim¹, Min-Su Kim¹, and Jin-Goo Park^{1,2}
소속: ¹Department of Bionano Technology, Hanyang University, ²Department of Materials Engineering, Hanyang University